ABSTRACT
This application report addresses three key criteria for selecting an ESD device for protecting high-speed signals. As the industry continues to trend towards smaller chipset features sizes to address higher speed data rates, tolerance of transient voltages has continued to shrink as well. Picking the right ESD device the first time is critical to preventing costly board re-spins during EMC testing. By using the three techniques discussed in this paper, device selection can be greatly simplified and streamlined.

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1 Introduction
When designing a system to support high speed interfaces such as USB 3.1 Gen 2, HDMI 2.0, DisplayPort 1.3, or Thunderbolt, a designer must take into account the entire system in order to meet all end customer requirements. When selecting a TVS diode device, two important criteria come into account: does this device’s added capacitance still allow my signals to pass cleanly, and does this device provide the necessary protection from transient events such as ESD? This paper discusses three techniques that can be applied to satisfy the two main TVS diode requirements. Those techniques are:

• TLP analysis – to understand the system breaking point, and the right device to protect it
• Eye diagram analysis – to show what effect a TVS diode has on the system eye diagram
• Layout considerations – best practices that can improve ESD performance and signal integrity

2 TLP Analysis
The TLP (Transmission Line Pulse) test is an efficient way to characterize a protection structure’s performance during ESD events. Since TLP has a similar transient duration as IEC 61000-4-2 ESD events and regular waveform shapes, it is common to use this test for assessing how well an ESD device clamps during the IEC strikes. The lower voltage a TLP curve shows for a certain current level, the better it clamps for ESD, which provides more protection for the sensitive ICs behind it.
The TLP technique is realized by charging a long, floating cable and discharging it into the DUT (Device Under Test) at successively increasing levels. The discharging pulses occur within a short duration of 100 ns. Gradually increasing currents and the according voltages are averaged over a time range during the pulse (usually 70%-90% of the pulse duration) and each pulse get recorded. Each current and voltage pair then defines a point on the TLP I-V curve as shown in Figure 1.

![Figure 1. TLP Measurement Example](image)

The TLP curve resembles the DC I-V curve but it characterizes the DUT’s transient clamping behavior. Since the test is only carried out over a very short period, the current can run at much higher levels than a DC sweep. Important information like snapback behavior and dynamic resistance can be extracted from the TLP curve.

TLP can be destructive at high levels. There is usually an apparent shift on the TLP curve when the DUT fails. A more reliable criterion to identify failure is a DC I-V sweep after each TLP pulse. The failure level is defined at the point where it starts to show excessive leakage after the pulse. The failure point from TLP is indicative of that from an ESD event.

A general guideline for correlating TLP current with IEC voltage level is as follows:
- IEC 1-kV level = 2 A, 100 ns TLP pulse
- IEC 2-kV level = 4 A, 100 ns TLP pulse
- IEC 4-kV level = 8 A, 100 ns TLP pulse
- Etc...

TLP is an effective tool for evaluating the transient robustness of a system that includes both protection devices and the protected ICs. By using the TLP test, one can determine the protection device performance needed for the protected IC. Figure 2 shows the TLP curve of an IC that needs to be protected. Without any protection, it fails at ±3 A, which translates to only 1.5-kV IEC 61000-4-2 ESD.
Figure 2. Example IC TLP Results

If the goal is to pass +8-kV IEC 61000-4-2 contact discharge, the protection device and the TVS should withstand at least 16 A of current and keep the clamping voltage below the failure point of the protected IC.

TI's TPD1E04U04 is a superior ESD protection device with low capacitance and dynamic resistance which enables the part to operate at a high-speed data rate and protects downstream ICs with an extremely low clamping voltage. In this example, at 9 V and –5.5 V, TPD1E04U04 adds ±18 A current handling capability during TLP tests, which are equivalent to ESD. This adds ±9-kV IEC 61000-4-2 capability, making the whole system IEC 61000-4-2 ESD compliant up to ±10.5 kV. Figure 3 shows the example IC TLP curve with TPD1E04U04's TLP results overlaid on top. The corresponding IEC 61000-4-2 passing level is shown on the right axis.

Figure 3. Example IC TLP Results with TPD1E04U04 Superimposed
3 Eye Diagram Analysis

For most high speed differential signals the eye diagram test is the final authority on signal integrity. By testing the eye diagram, many different measurements can be captured which allows for quick understanding of the problem in a system. A TVS diode generally affects eye diagrams by slowing the rise and fall times due to the inherent capacitive loading of the TVS. However, choosing the correct TVS diode for the application should only degrade the eye diagram minimally. The examples in Figure 4 and Figure 5 show USB 3.1 Gen 2 (10-Gbps) eye diagram with and without our TPD1E01B04.

![Figure 4. USB 3.1 Gen 2 10-Gbps Eye Diagram (Bare Board)](image)

As it is seen in the USB 3.1 Gen 2 10 Gbps Compliance Test, the above tests show almost no difference in eye diagram performance. This is due to the extremely low capacitive loading (0.2-pF maximum). For more details on eye diagram performance and the impact of TVS diodes on signal integrity, see the application report Capacitance Requirements for High Speed Signals, SLVA793.
4 Layout Considerations

Board layout is an important factor to get the best system performance in protection and other aspects like signal integrity. By following these ESD layout guidelines it can be ensured that the protection device gets optimum performance in the system.

- General ESD layout best practices:
  - In order to discharge the ESD before it couples onto anything close to it, place the protection devices as near to the connector as design rules allow
  - Place the Protected IC much further from the protection device than the protection device is to the connector
  - Do not use stubs between the ESD source and protection device, route directly from the ESD source to protection
  - In order to conduct most current into the ESD device and keep the clamping voltage low, minimize any inductance between the ESD Source and the path to ground through the TVS

- Use a grounding scheme that has very low impedance:
  - Connect the protection device Ground Pin directly to a same layer ground plane that has nearby VIAs stitching to an adjacent internal ground plane
  - Use multiple ground planes when possible
  - Use VIAs of large diameter with a large drill, which lowers impedance

- Limit the effects of EMI on unprotected circuits:
  - Do not route unprotected circuits in the area between the ESD Source and the TVS to minimize EMI coupling onto unprotected traces
  - Route with straight traces between the ESD Source and the protection device if possible
  - Avoid using sharp corners in routing since electric fields tend to build up on corners, increasing EMI coupling

Also, the number of VIAs should be kept to minimum for high speed data lines. Take USB Type-C data lines as an example (Figure 6), there are four SuperSpeed TX-RX data lines on each end of the connector. This is split into four on each side of a two-layer board. A four-channel ESD device is a popular choice for many applications, but for Type-C connectors that have 20-Gbps differential pairs it may not be the best option since VIAs are needed to route all four data lines to the same layer. This issue can be mitigated by using single or dual channel ESD devices.

![Figure 6. Example Layout with 4-Channel Routing Inefficiencies](image)

5 Conclusion

Today’s high-speed signals can be challenging to design. This application note provides three helpful techniques to simplify EMC design and aid in success. TI’s TVS diode portfolio provides a large variety of choices for high-speed data line protection to meet customer requirements.
6 References

- TI's ESD portfolio (ti.com/esd)
- Reading and Understanding an ESD Protection Datasheet (SLLA305)
- ESD Protection Layout Guide (SLVA680)
- Capacitance Requirements for High Speed Signals (SLVA793)
- TPD1E04U04
- TPD1E01B04
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